University of Glasgow

HIGH FREQUENCY COMMUNICATION SYSTEMS

Lecture 11

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Figure 1: Survey available at https://forms.office.com/r/uzegCvGdPE.

- Terahertz Communications
- Terahertz Generation
- Plasmonics
- Applications of Terahertz

TERAHERTZ COMMUNICATIONS

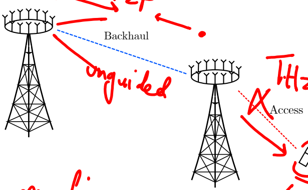
THE TERAHERTZ SPECTRUM

- The electromagnetic (EM) spectrum between 0.1 THz to 10 THz is called the *THz band*.

300 GHz – 30 THz

3 – 6 GHz

- Naturally, higher carrier frequency yields higher bandwidth
  - Not necessarily higher channel capacity
- We can achieve bandwidths up to 20 Gbps
  - A typical 8K film requires 200 Mbps bandwidth!
  - For comparison, optical fibre communication can provide 39 Tbps bandwidth! guided medium
- THz communications provide a promising application for back hauling of base stations.



P2P

unguided

THz

range ↓

~GB
1 – 10 THz @ ~cm

[NFC
RFID]

8 kb

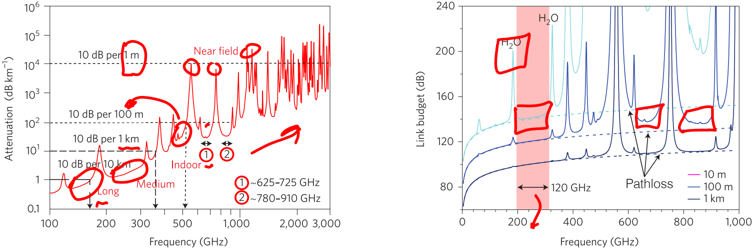
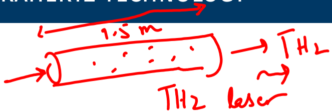
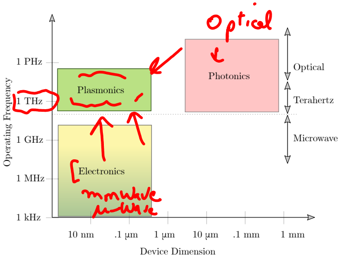


Figure 2: EM wave attenuation and free-space path-loss due to H_2O molecules in the air in the THz spectrum [Nagatsuma, T., *et al.* Nature Photon 10, 371-379 (2016)].

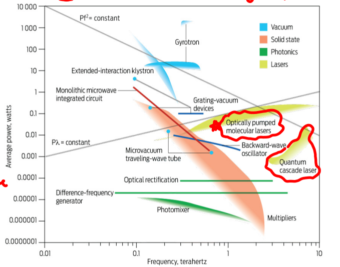


1 cm
50 μm

- Just like mmWave communications, THz waves have considerably high free-space pathloss
  high size ~ λ
  - This requires even higher gain antennas (∼ 100 dB)
- Current THz device technology does not allow us to increase the power levels
- Since THz lies in the middle of microwave and optical frequencies, we get the *best of both worlds*.
  photo
  O
  molecule
  - We have non-ionising waves
  - We can construct devices similar to optical technologies.

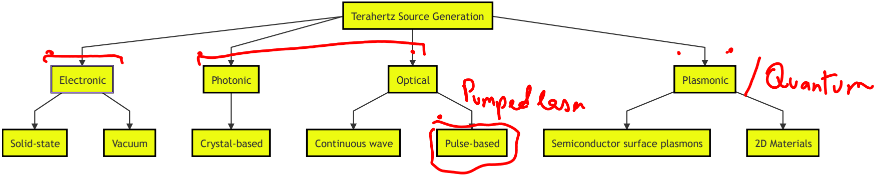


Carbon CO_2 -gas laser 3-7 THz



TERAHERTZ SOURCES

There are many ways to generate efficient THz signals. However, all the technologies have not fully developed to be widely available.



Today, we will focus on the plasmonic technologies.

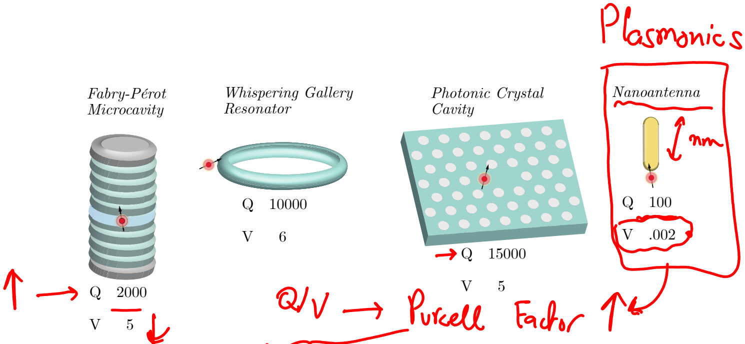


Figure 3: Different Source techniques at THz and optical frequencies.

- Microwave based vacuum tube technologies are extended to THz frequencies
  - The process involves conversion of modulated electron current to electromagnetic radiation
  - These are often called *fast-wave* devices
  - The phase velocity of the generated electromagnetic wave is greater than the speed of light

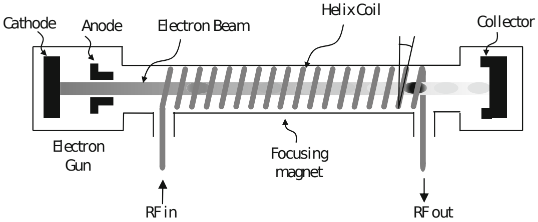
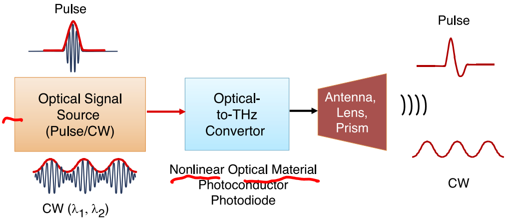


Figure 4: A typical vacuum-tube source [Rieh, J-S., Intro to Terahertz Electronics, Springer (2021)].



- The main idea is the optical-THz signal conversion through lasers
- Non-linear optical (NLO) materials are used to generate *monochromatic* THz waves
  - II-VI Semiconductor crystals such as ZnTe, and CdTe are commonly used as NLO materials

PLASMONICS

4th Plasma

• gas
• liquid
• solid

Plasma → volumetric
Plasmonic → surface (interface)

- Interfacial wave phenomena
    - Metal-dielectric interface
    - Semiconductor heterostructure
- Surface plasmon polaritons (SPPs)
- Plasma frequency — resonance of free electron
    - Metals — Optical frequency
    - Semiconductors — Terahertz

Gold, Silver, Aluminum

GaAs GaN III-V

CMOS

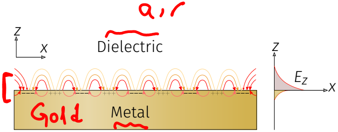


Figure 5: SPPs at optical frequencies

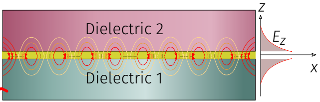


Figure 6: SPPs in the THz regime

gold : 633 nm (green)

100 times slower

- Slow surface waves
- Reduced Wavelength
- Focusing beyond the diffraction limit
- Optical SPP

noble metals

$$\mathrm{Re}\left[\varepsilon_{\text{metal}}(\omega)\right] < 0$$

- THz SPP

III-V

$$\mathrm{Im}\left[\sigma_{\text{s}}(\omega)\right] < 0$$

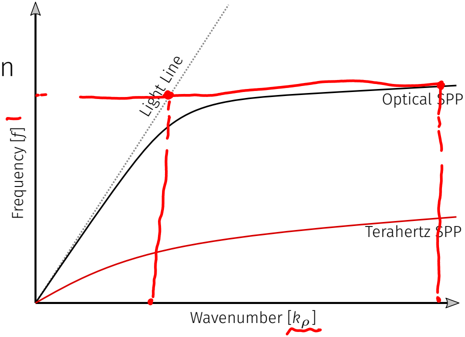


Figure 7: Dispersion Curve comparison

$k_p = \frac{2\pi}{\lambda}$

- Convert Localized near-field to efficient far-field radiation
- Low Q-factor
- Extremely small size
- High Purcell Factor

$$P = \frac{Q}{V}$$

- Directive radiation

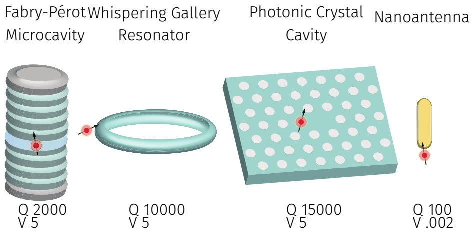
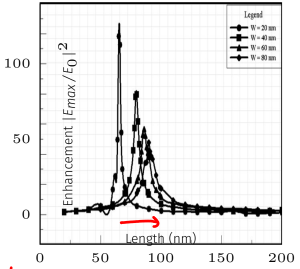


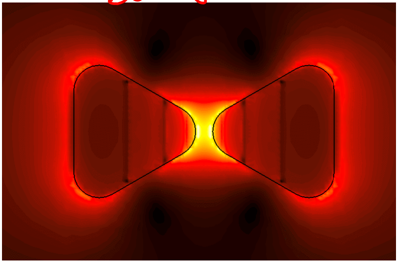
Figure 8: Optical resonant cavities for electric field enhancement

- Scaled-down microwave antenna designs
- Shift of resonance with width unlike in microwave regime

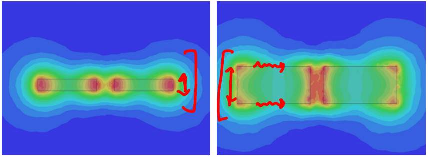
Resonant frequency ~f(L, W)



Bowtie



Dipole



Plasma [free electrons] → are at the surface.

- Semiconductor Heterostructure in high electron mobility transistor (HEMT)
- High concentration of free electrons ($\sim 1 \times 10^{11} - 1 \times 10^{14}\,\text{cm}^{-2}$)
- Very high Mobility ($\sim 1 \times 10^{3} - 1 \times 10^{6}\,\text{cm}^{2}/\text{V/s}$)
- Formation of Quantum Well
  - Two-dimensional confinement of electrons

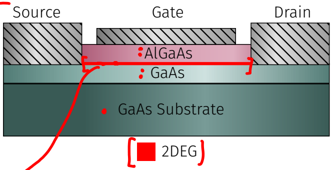


Figure 9: Typical GaAs/AlGaAs HEMT

10^{23}

MOSFET

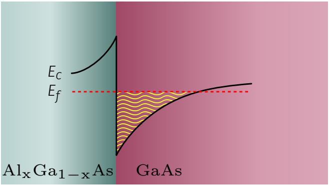
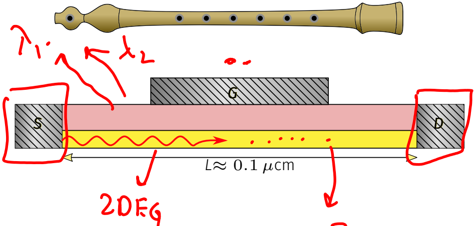


Figure 10: Band diagram of a GaAs/AlGaAs heterostructure

2DEG (contd.)

- Plasma waves in 2DEG
- Dyakonov-Shur instability
  - Voltage bias at source and drain terminals
  - Plasma resonance
  - THz emission
- Electronic Flute
  - Tunable resonance with gate voltage



$$\lambda = \frac{c}{f}$$

$$\implies 300\mu\text{m}$$

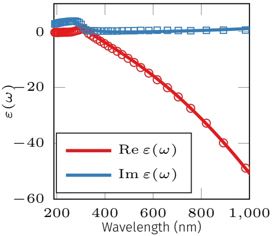
- SPP solution (pole expression)

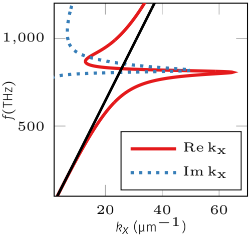
$$k_{sp} = \frac{\omega}{c}\sqrt{\frac{\varepsilon_1 \varepsilon_2(\omega)}{\varepsilon_1 + \varepsilon_2(\omega)}}$$

- Accurate material description

$$\varepsilon_2(\omega) = \varepsilon_\infty - \frac{\omega_d^2}{\omega^2 - j\gamma\omega} + \sum_{i=1}^{N} G_i(\omega)$$

$$G_i(\omega) = C_i \left[\frac{e^{j\phi_i}}{\omega_i + \omega - j\Gamma_i} + \frac{e^{-j\phi_i}}{\omega_i - \omega + j\Gamma_i} \right]$$





- Drude-Lorentz Surface Conductivity

$$\sigma_S = \frac{N_S e^2}{m^*} \frac{\tau}{1 + j\tau\omega}$$

N_S - Surface charge density

τ - Scattering time

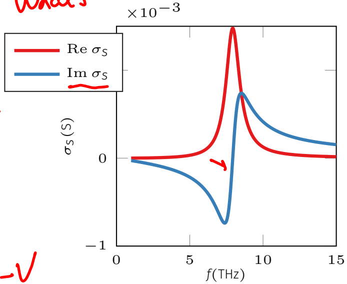
m^*- Effective electron mass

- Equivalent Circuit

$$\sigma_S = \frac{1}{Z} = \frac{1}{R + 1/j\omega C}$$

- Graphene
- Wan der Waal's heterostructure

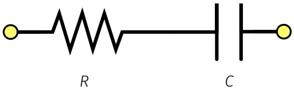
2D material



III-V

Figure 11: Room temperature GaN/AlGaN 2DEG surface conductivity

$Z = R - \frac{j}{\omega C}$



- Conductive Sheet in free space
- TM mode surface wave

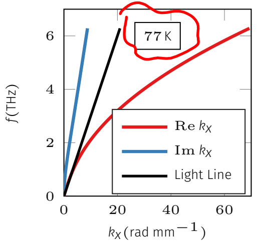
$$k_{\mathrm{P}}^{\mathrm{TM}} = \frac{\omega}{c}\sqrt{1 - \left(\frac{2}{\eta_0 \sigma_s}\right)^2}$$

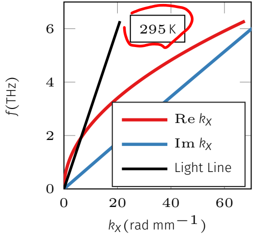
- Below plasma frequency

$$\mathrm{Im}\,\sigma_s < 0$$

- At low temperature

$$\mathrm{Im}\,|\sigma_s| \gg \mathrm{Re}\,|\sigma_s|$$





Relying on the principle of reciprocity, we can use photoconductive antennas to detect THz radiation.

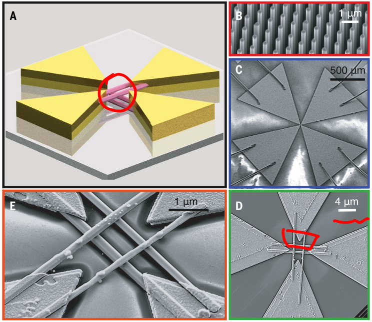
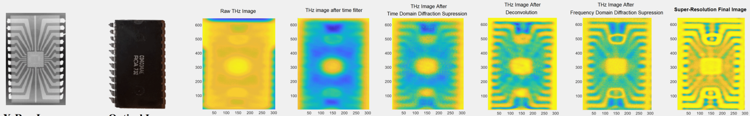


Figure 12: A polarisation sensitive cross-nanowire THz detector [Peng et al., Science 368, 510-513 (2020)].

- THz waves have the ability to see through apparently opaque objects.
- This is done in a non-ionising manner (preferable for biological applicn
- Through image processing, we can achieve high-resolution imaging through THz waves.



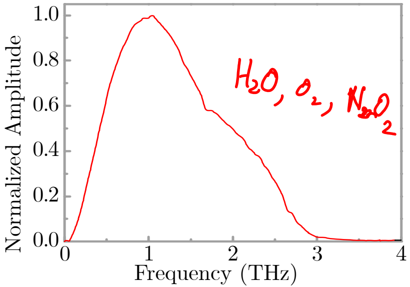
X-Ray Image

Optical Image
(a packaged IC)

High resolution Terahertz Image and steps of developing it

THz → finger printing regin

- THz time-domain spectroscopy (THz-TDS) is a well-known method for charaterising the material properties of different substances
    - Attractive applications in explosives detection, counterfeit drug discovery and health monitoring of plants
- The Biggest feature is again, the non-ionising nature of THz waves
- Common substances such as H_2O and N_2 have strong absorption spectra



2,4,6-Trinitrotoluene (TNT)